

Electronic Acknowledgement Receipt

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International Application Number:	
Confirmation Number:	3451
Title of Invention:	Method for Self-Supported Transfer of a Fine Layer by Pulsation after Implantation or Co-Implantation
First Named Inventor/Applicant Name:	Nguyet-Phuong Nguyen
Customer Number:	90678
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File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/ Message Digest	Multi Part /.zip	Pages (if appl.)
1	NPL Documents	Eaglesham_et_al.pdf	272298 <small>56026e891bcd7813254578fcd7de7e3d22897b</small>	no	4

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2	NPL Documents	EerNisse_1973.pdf	768866 8a4542aa7694731b330576c3a259a35381761c2	no	8
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3	NPL Documents	EerNisse_et_al_1977.pdf	801341 c1ca258beaef755d11186ca2755db5d79cd1a30	no	9
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9	NPL Documents	Goesele_et_al_Semiconductor_Wafer_Bonding.pdf	1371808 2cd879aldcb7bd87e6c584a053337cd8c2e0527a0d	no	28
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13	NPL Documents	Haisma_et_al_Silicon_on_Insulator-Wafer_Bonding.pdf	1279237 3c19415ab698227c4b4895963b58aef1c18a2cf	no	18
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26	NPL Documents	Jones_et_al.pdf	379786 d146090d4889595956ba9c8a0b8f3875c ed705	no	4
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34	NPL Documents	Ligeon_E-Hydrogen_Implantation_in_Silicon_Between_1-5_and_60_KeV.pdf	820674 278dc18c1ad21c581c8a7280bd3459a2c0ab1	no	9
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55	NPL Documents	Myers_DR-The_Effects_of_Ion-Implantation_Damage_on_The_First_Order_Raman_Spectra.pdf	676976 580226c3c3a65981152880b0a03ed7b7c4d2f7c	no	7
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56	NPL Documents	Neethling_CE_et_al_Identification_of_Hydrogen_Platelets_in_Proton_Bombardment_GaAs.pdf	436026 b6b5c5d5488ca4b1961482af23b378d997	no	5
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New Applications Under 35 U.S.C. 111

If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.

National Stage of an International Application under 35 U.S.C. 371

If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.

New International Application Filed with the USPTO as a Receiving Office

If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.